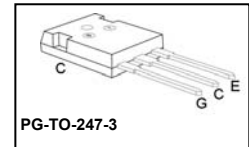
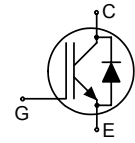


**TrenchStop® Reverse Conducting (RC-)IGBT with monolithic body diode**
**Features:**

- Powerful monolithic Body Diode with very low forward voltage
- Body diode clamps negative voltages
- Trench and Fieldstop technology for 1600 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>


**Applications:**

- Inductive Cooking
- Soft Switching Applications

Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_J=25^\circ C}$	$T_{j,max}$	Marking	Package
IHW30N160R2	1600V	30A	1.8V	175°C	H30R1602	PG-TO-247-3

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1600	V
DC collector current $T_C = 25^\circ C$ $T_C = 100^\circ C$	$I_C$	60 30	A
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{C,puls}$	90	
Turn off safe operating area ( $V_{CE} \leq 1600V, T_j \leq 175^\circ C$ )	-	90	
Diode forward current $T_C = 25^\circ C$ $T_C = 100^\circ C$	$I_F$	60 30	
Diode pulsed current, $t_p$ limited by $T_{j,max}$	$I_{F,puls}$	90	
Diode surge non repetitive current, $t_p$ limited by $T_{j,max}$ $T_C = 25^\circ C, t_p = 10ms$ , sine halfwave $T_C = 25^\circ C, t_p \leq 2.5\mu s$ , sine halfwave $T_C = 100^\circ C, t_p \leq 2.5\mu s$ , sine halfwave	$I_{FSM}$	50 130 120	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Transient Gate-emitter voltage ( $t_p < 10 \mu s, D < 0.01$ )		$\pm 25$	
Power dissipation $T_C = 25^\circ C$	$P_{tot}$	312	W
Operating junction temperature	$T_j$	-40...+175	°C
Storage temperature	$T_{stg}$	-55...+175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>1</sup> J-STD-020 and JESD-022

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.48	K/W
Diode thermal resistance, junction – case	$R_{thJCD}$		0.48	
Thermal resistance, junction – ambient	$R_{thJA}$		40	

### Electrical Characteristic, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	1600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=30A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.8	2.1	
			-	2.25	-	
			-	2.35	-	
Diode forward voltage	$V_F$	$V_{GE}=0V, I_F=30A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.65	2.0	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.75mA,$ $V_{CE}=V_{GE}$	5.1	5.8	6.4	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1600V,$ $V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	-	5	$\mu A$
			-	-	2500	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=30A$	-	22.5	-	S
Integrated gate resistor	$R_{Gint}$			none		$\Omega$

### Dynamic Characteristic

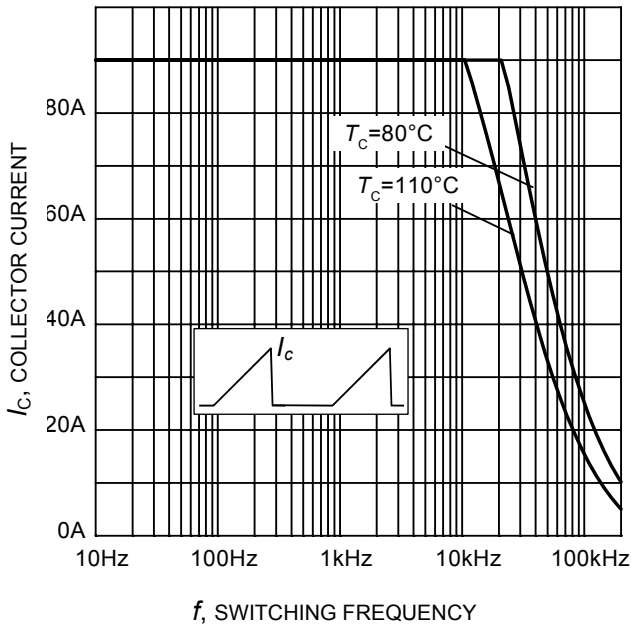
Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$	-	2740	-	pF
Output capacitance	$C_{oss}$		-	68.1	-	
Reverse transfer capacitance	$C_{rss}$		-	58.7	-	
Gate charge	$Q_{Gate}$	$V_{CC}=1280V,$ $I_C=30A; V_{GE}=15V$	-	94	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13	-	nH

### Switching Characteristic, Inductive Load, at $T_j=25^\circ C$

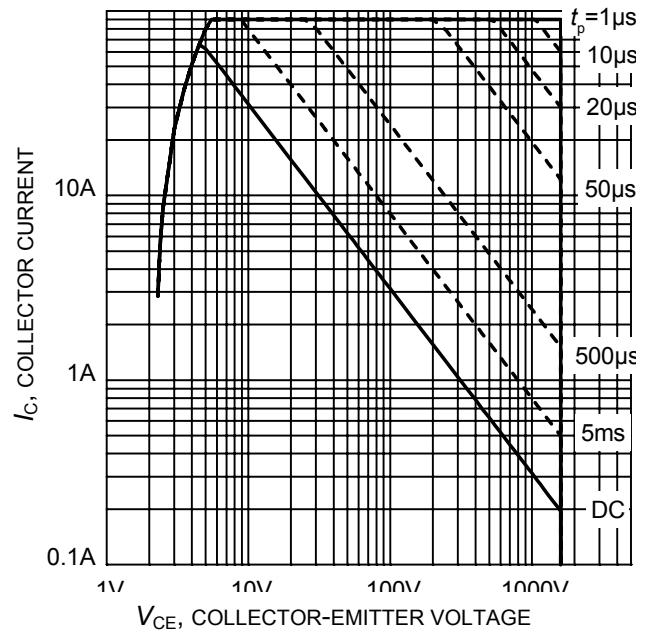
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-off delay time	$t_{d(off)}$	$T_j=25^\circ C,$ $V_{CC}=600V, I_C=30A$ $V_{GE}=0 / 15V,$ $R_G=10\Omega$	-	525	-	ns
Fall time	$t_f$		-	38.3	-	
Turn-on energy	$E_{on}$		-	-	-	
Turn-off energy	$E_{off}$		-	2.53	-	mJ
Total switching energy	$E_{ts}$		-	2.53	-	

### Switching Characteristic, Inductive Load, at $T_j=175^\circ C$

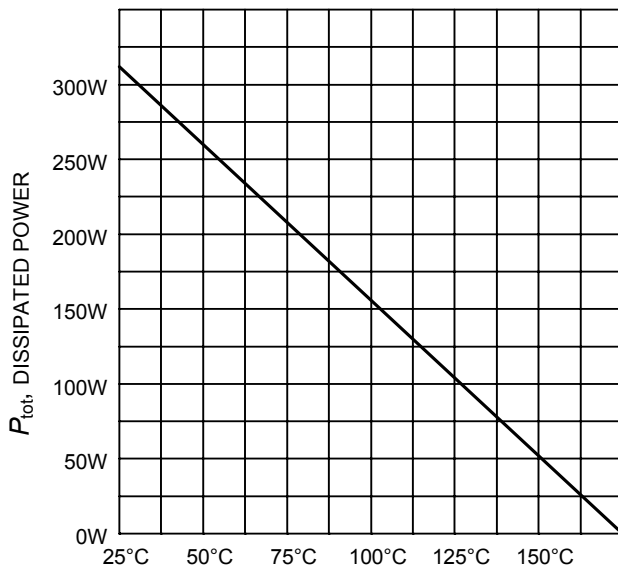
Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>IGBT Characteristic</b>						
Turn-off delay time	$t_{d(off)}$	$T_j=175^\circ C$ $V_{CC}=600V, I_C=30A,$ $V_{GE}= 0 / 15V,$ $R_G= 10\Omega$	-	564	-	ns
Fall time	$t_f$		-	111	-	
Turn-on energy	$E_{on}$		-	-	-	
Turn-off energy	$E_{off}$		-	4.37	-	mJ
Total switching energy	$E_{ts}$		-	4.37	-	



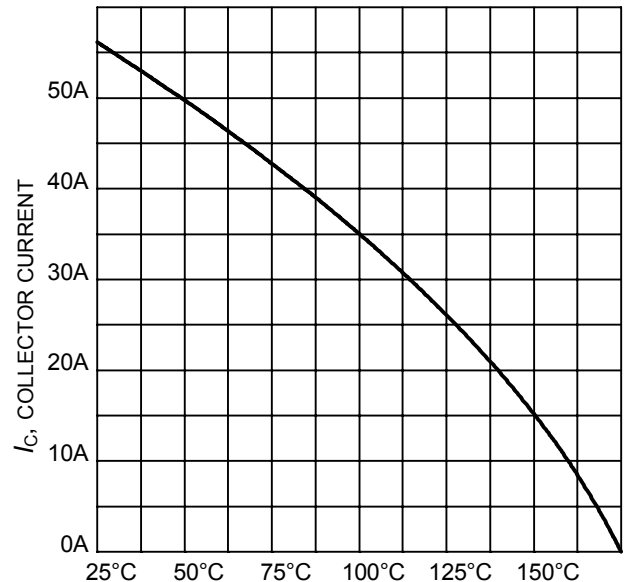
**Figure 1. Collector current as a function of switching frequency for hard switching (turn-off)**  
 ( $T_j \leq 175^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 600\text{V}$ ,  $V_{GE} = 0/+15\text{V}$ ,  $R_G = 10\Omega$ )



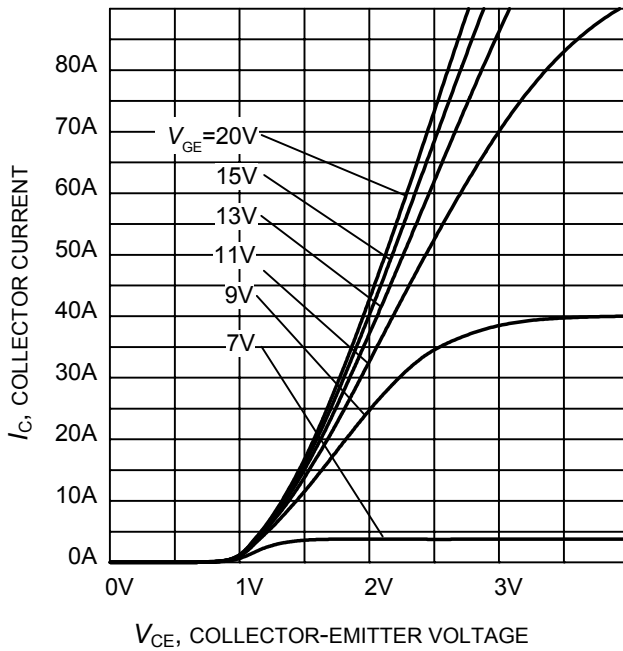
**Figure 2. IGBT Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 175^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$ )



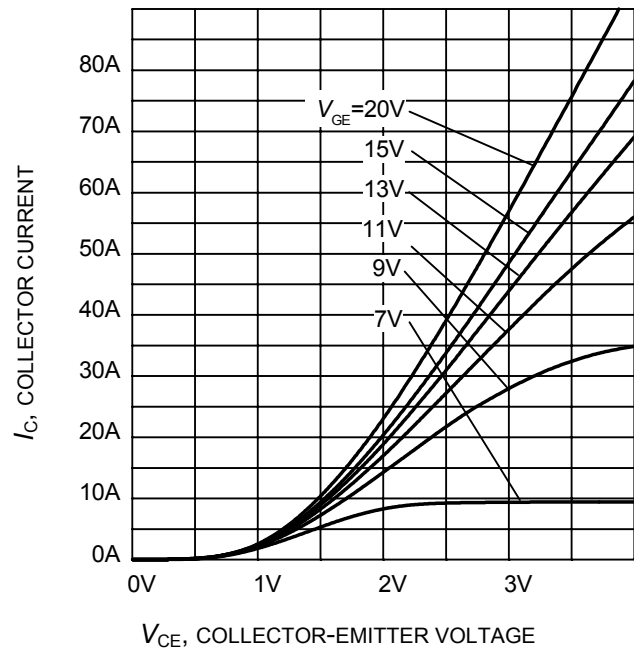
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 175^\circ\text{C}$ )



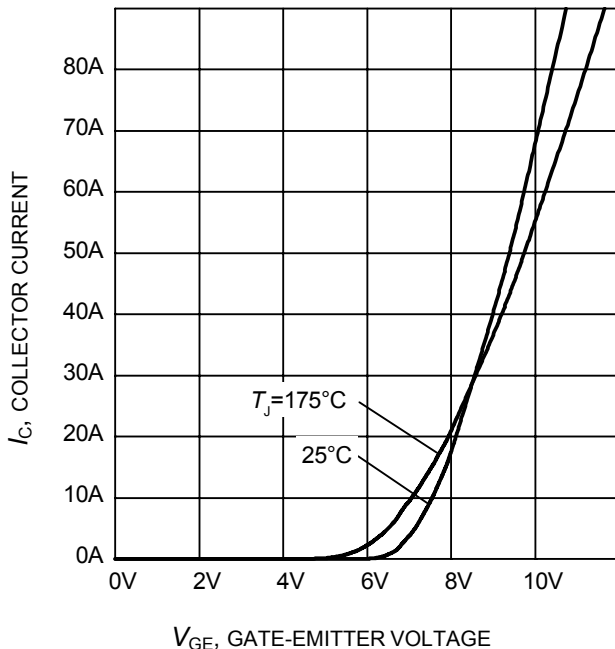
**Figure 4. DC Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 175^\circ\text{C}$ )



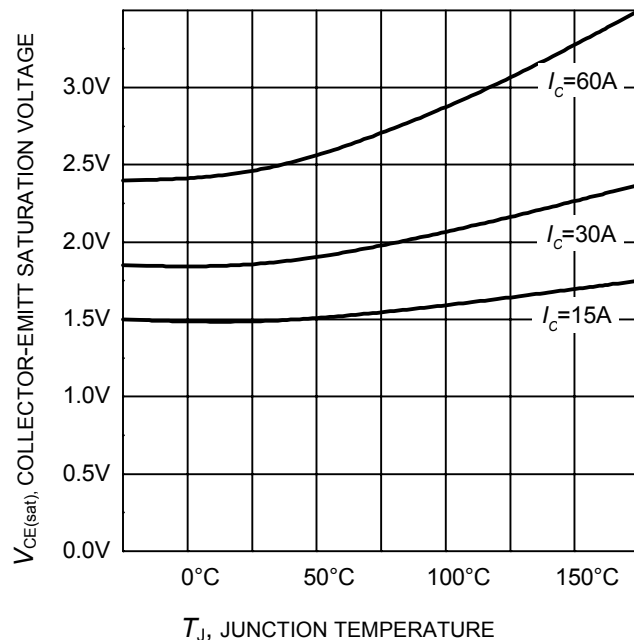
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



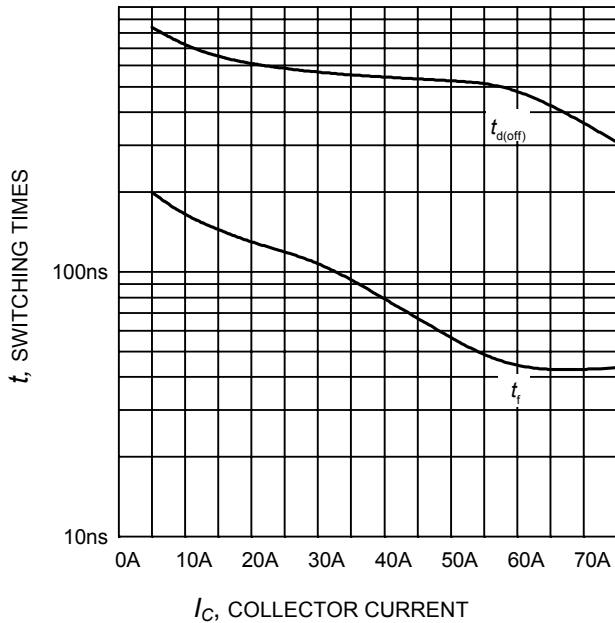
**Figure 6. Typical output characteristic**  
( $T_j = 175^\circ\text{C}$ )



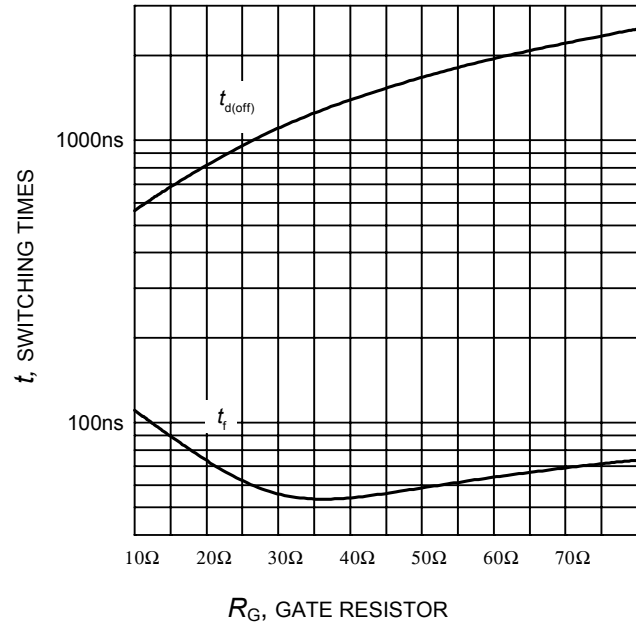
**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )



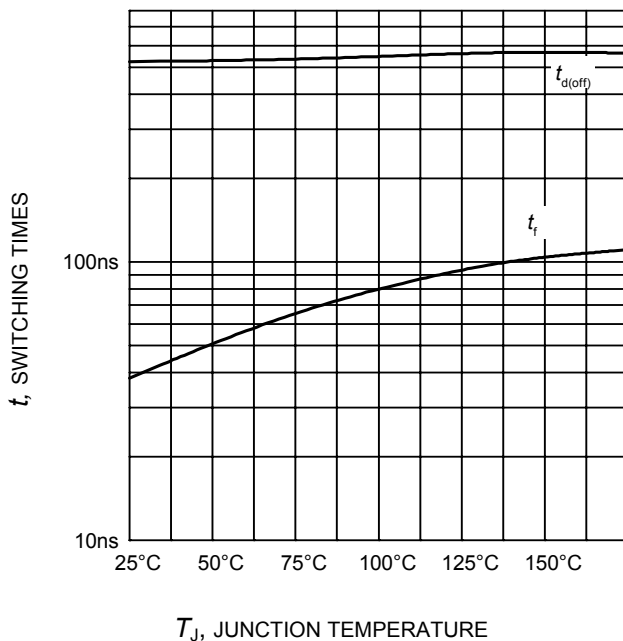
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



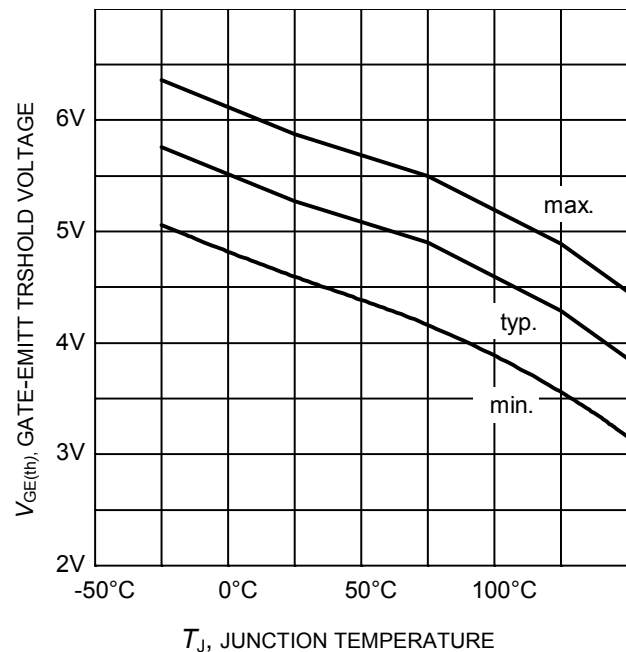
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



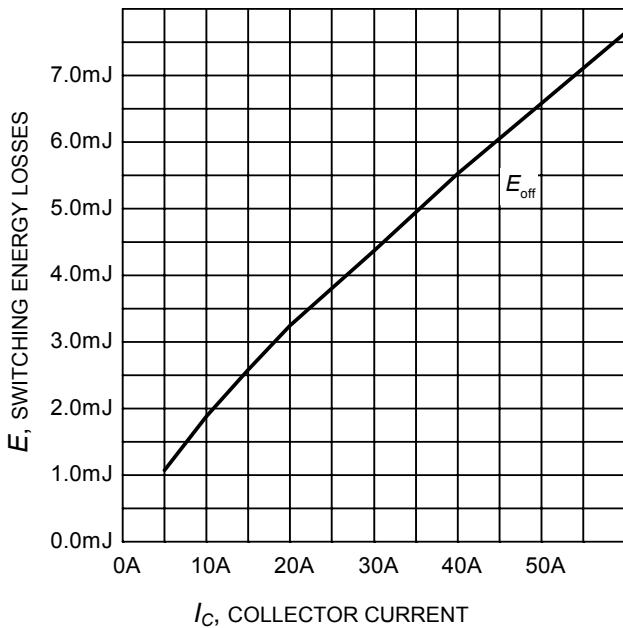
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=30\text{A}$ , Dynamic test circuit in Figure E)



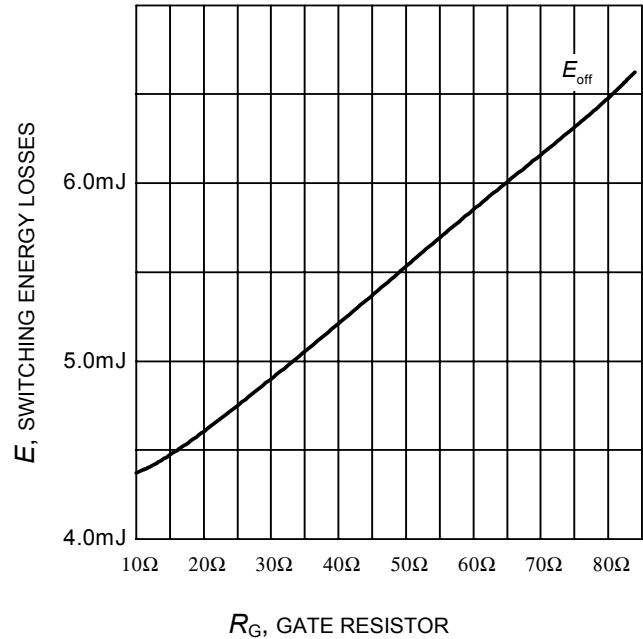
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=30\text{A}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



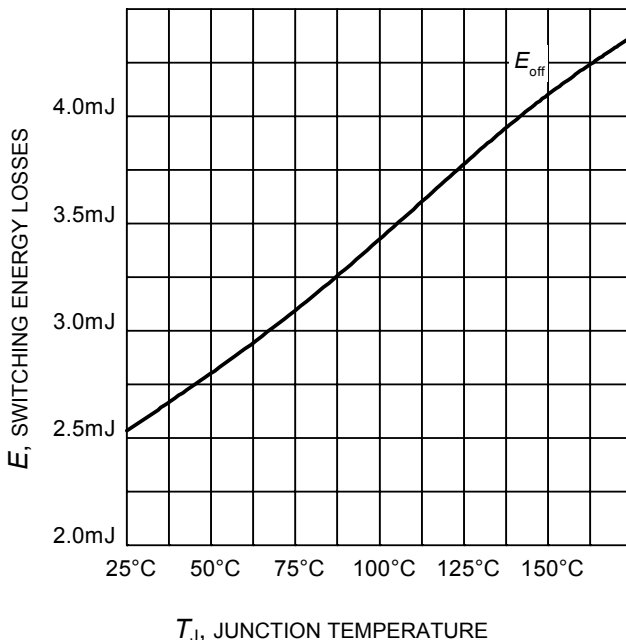
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.15\text{mA}$ )



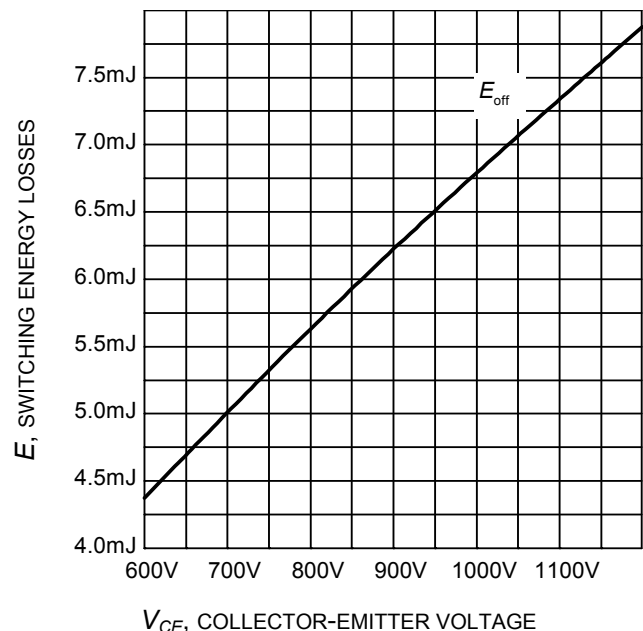
**Figure 13. Typical turn-off energy as a function of collector current**  
 (inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



**Figure 14. Typical turn-off energy as a function of gate resistor**  
 (inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=30\text{A}$ , Dynamic test circuit in Figure E)



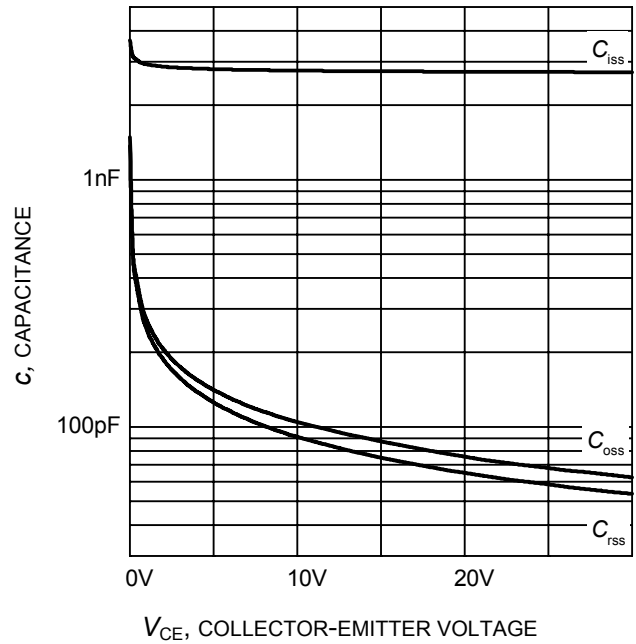
**Figure 15. Typical turn-off energy as a function of junction temperature**  
 (inductive load,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=30\text{A}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



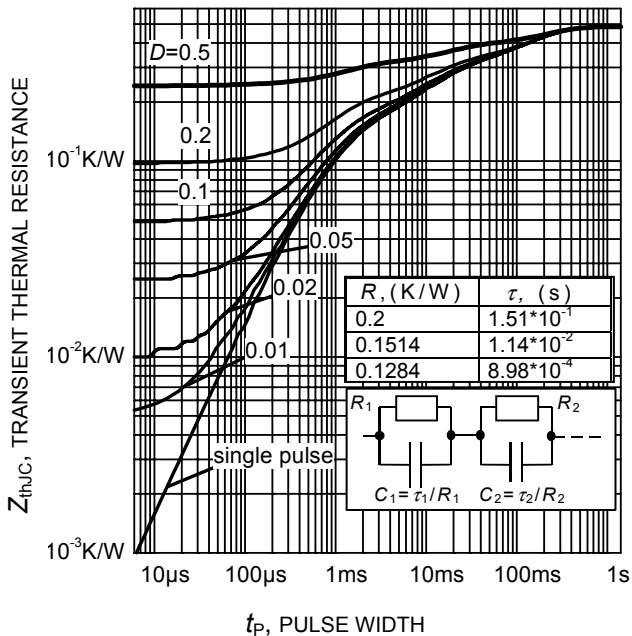
**Figure 16. Typical turn-off energy as a function of collector emitter voltage**  
 (inductive load,  $T_J=175^\circ\text{C}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=30\text{A}$ ,  $R_G=10\Omega$ , Dynamic test circuit in Figure E)



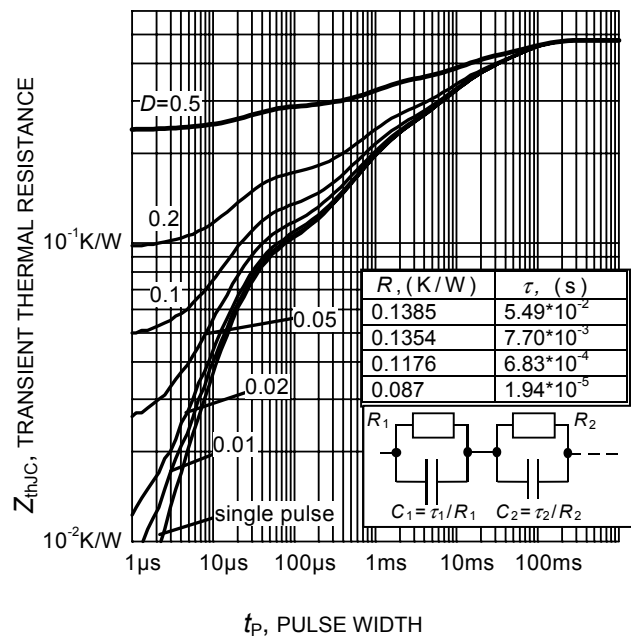
**Figure 17. Typical gate charge**  
( $I_C=30\text{ A}$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{ V}$ ,  $f = 1\text{ MHz}$ )

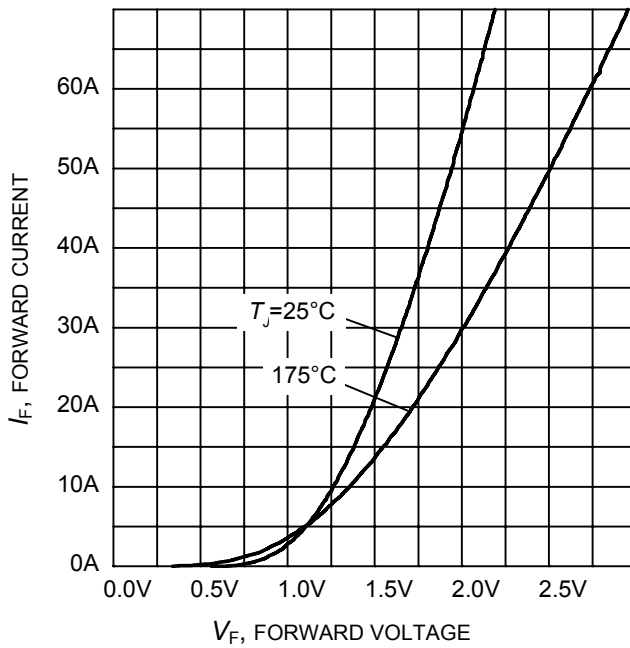


**Figure 19. IGBT transient thermal resistance**  
( $D = t_p / T$ )

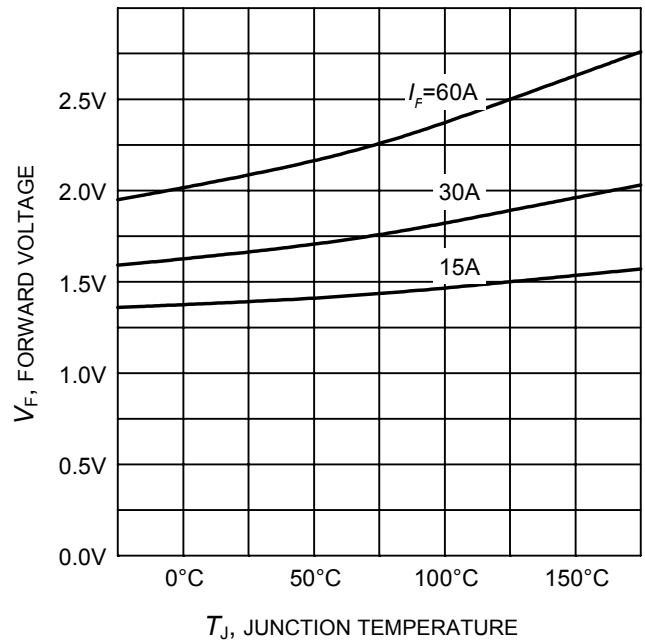


**Figure 20. Diode transient thermal impedance as a function of pulse width**  
( $D=t_p/T$ )



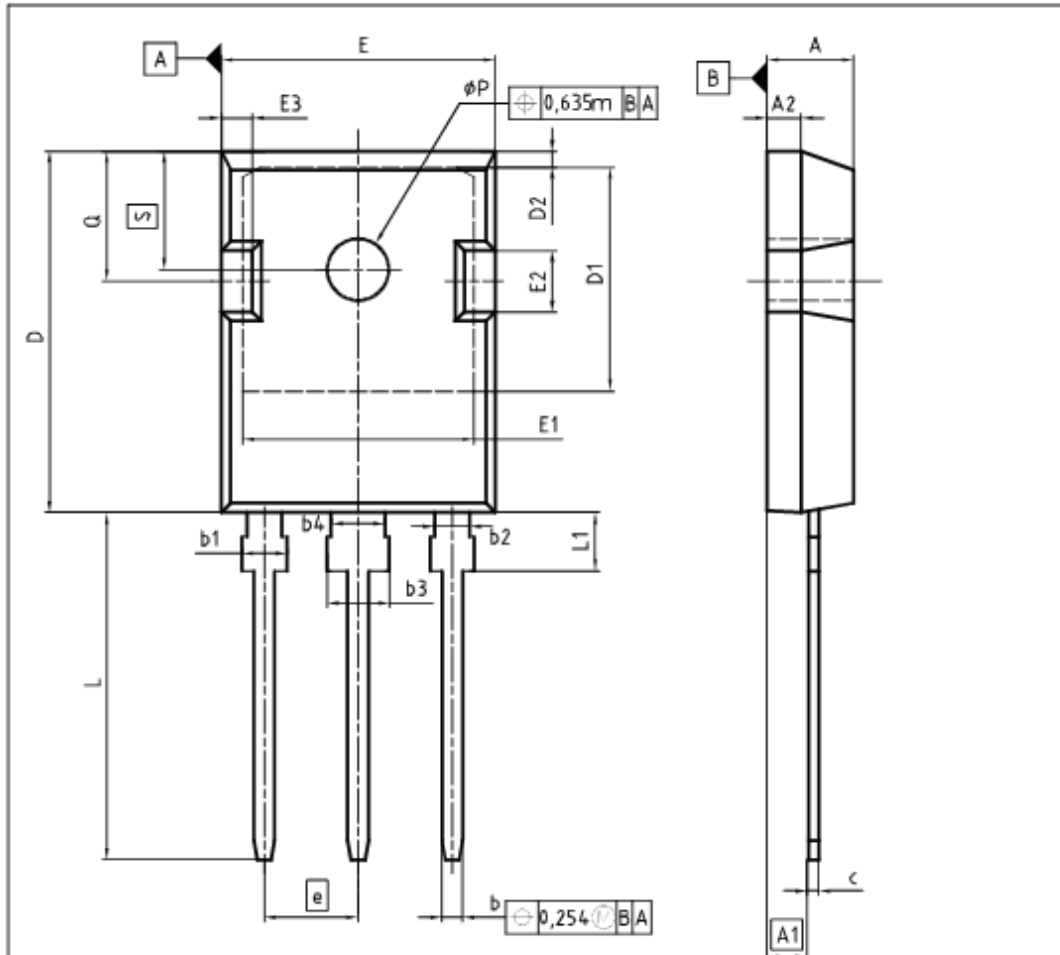


**Figure 21. Typical diode forward current as a function of forward voltage**



**Figure 22. Typical diode forward voltage as a function of junction temperature**

T0247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
φP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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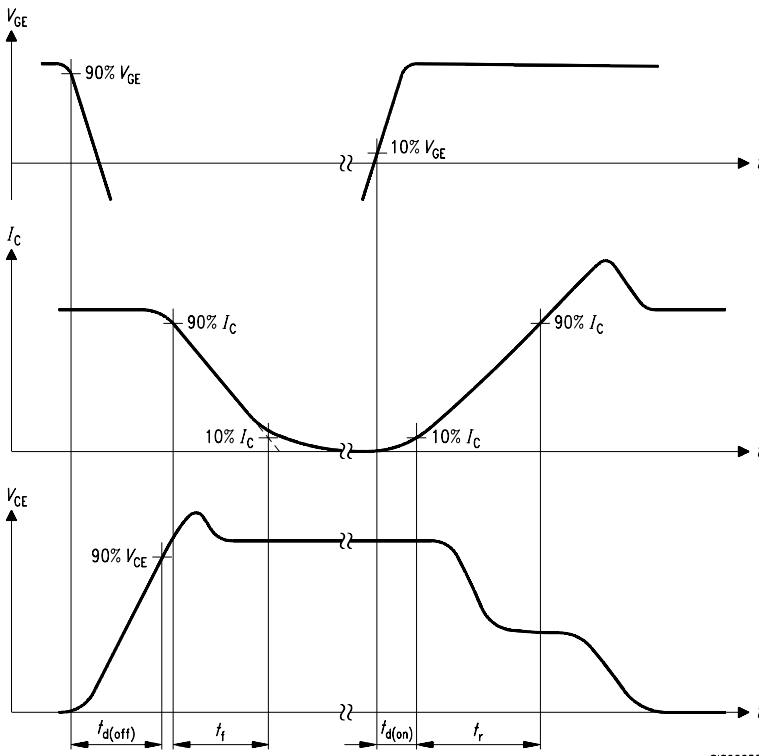


Figure A. Definition of switching times

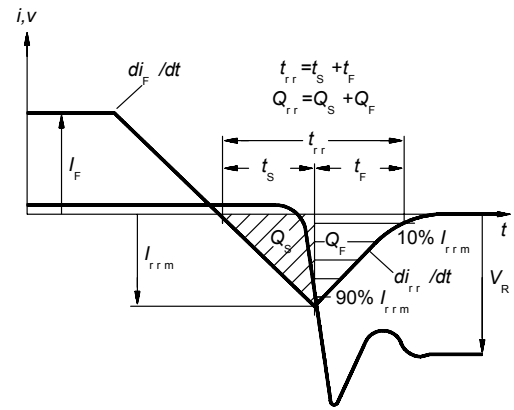


Figure C. Definition of diodes switching characteristics

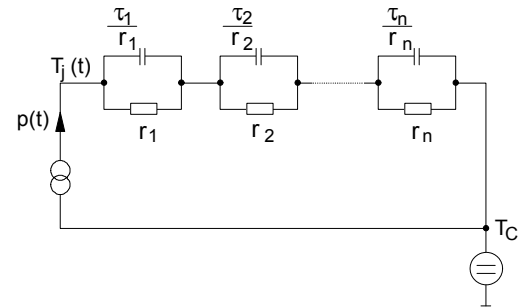


Figure D. Thermal equivalent circuit

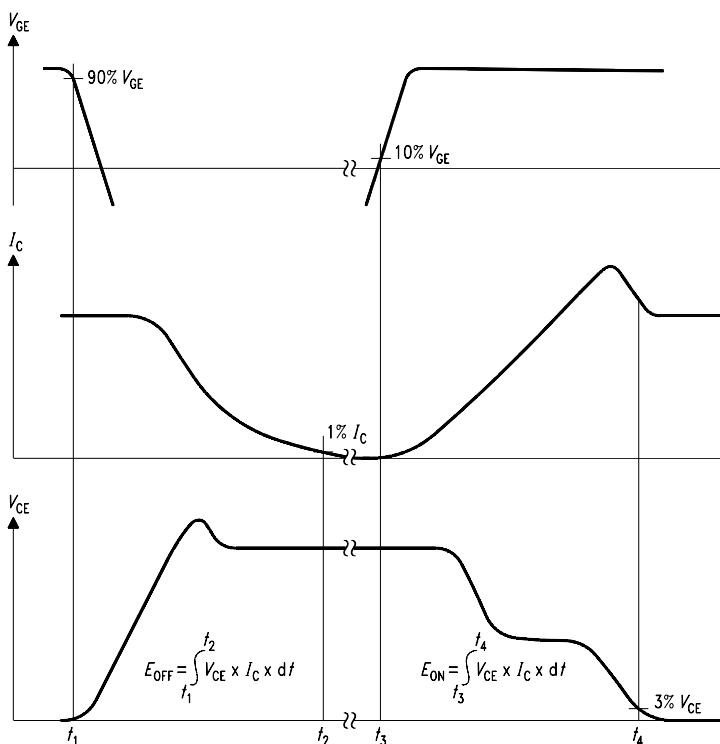


Figure B. Definition of switching losses

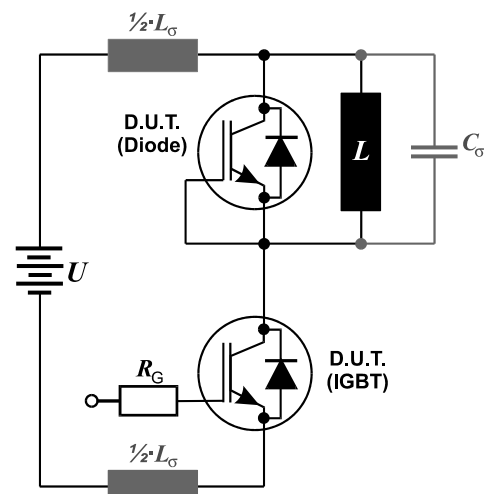


Figure E. Dynamic test circuit

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